



FIG. 4
Prior Art

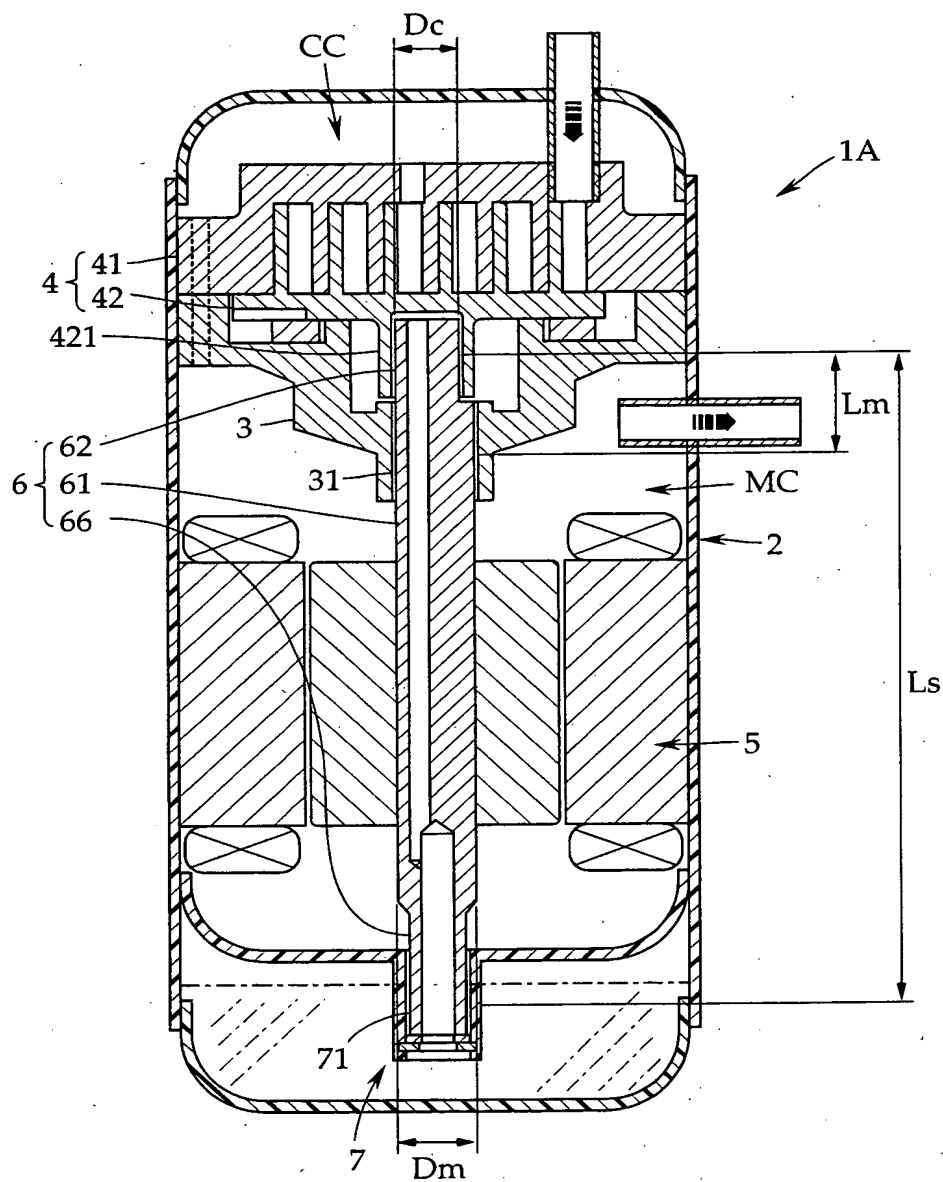




Fig. 1 is a cross-sectional view of a first embodiment of a semiconductor device. The device includes a substrate 1 with a central region 2. A central vertical structure 3 is surrounded by a ring-like structure 4, which is further divided into segments 41 and 42. A central vertical structure 31 is shown in cross-section, with a central opening 6. The device is surrounded by a protective layer 1B. Dimensions Dc and Dm are indicated.